

**Silicon PNP Power Transistor**

**2SA1214**

**DESCRIPTION**

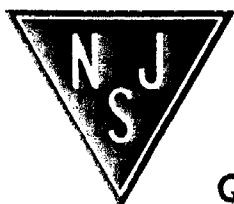
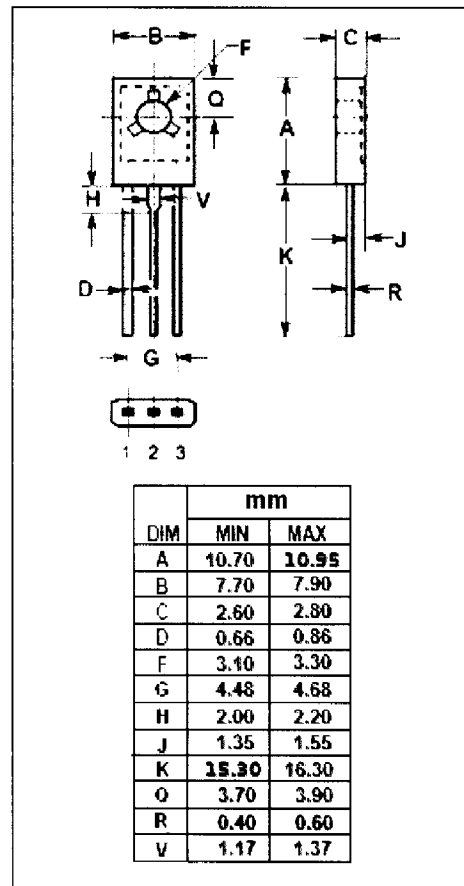
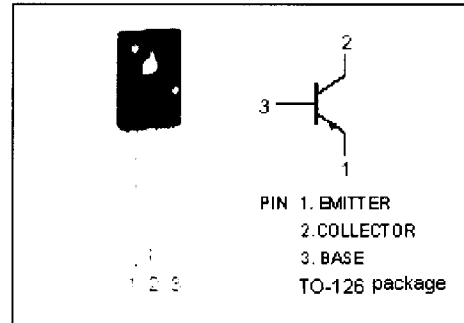
- Collector-Emitter Breakdown Voltage-  
 $V_{(BR)CEO} = -50V$  (Min)
- Good Linearity of  $h_{FE}$
- Wide Area of Safe Operation

**APPLICATIONS**

- Designed for low frequency power amplifier applications.

**ABSOLUTE MAXIMUM RATINGS(Ta=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-2	A
$P_C$	Collector Power Dissipation @ $T_a=25^\circ C$	1.5	W
	Total Power Dissipation @ $T_C=25^\circ C$	25	
$T_J$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature Range	-55~150	°C



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**Quality Semi-Conductors**

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### ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}; I_B = 0$	-50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -0.1\text{mA}; I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1\text{A}; I_B = -0.1\text{A}$			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -1\text{A}; I_B = -0.1\text{A}$			-1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -60\text{V}; I_E = 0$			-1.0	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-1.0	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -150\text{mA}; V_{CE} = -2\text{V}$	60		320	
$f_T$	Current-Gain—Bandwidth Product	$I_C = -100\text{mA}; V_{CE} = -10\text{V}$		35		MHz
$C_{OB}$	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f = 1.0\text{MHz}$		45		pF